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January 1999



### NMC27C64 65,536-Bit (8192 x 8) CMOS EPROM

### **General Description**

The NMC27C64 is a 64K UV erasable, electrically reprogrammable and one-time programmable (OTP) CMOS EPROM ideally suited for applications where fast turnaround, pattern experimentation and low power consumption are important requirements.

The NMC27C64 is designed to operate with a single  $\pm$ 5V power supply with  $\pm$ 10% tolerance. The CMOS design allows the part to operate over extended and military temperature ranges.

The NMC27C64Q is packaged in a 28-pin dual-in-line package with a quartz window. The quartz window allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written electrically into the device by following the programming procedure.

The NMC27C64N is packaged in a 28-pin dual-in-line plastic molded package without a transparent lid. This part is ideally

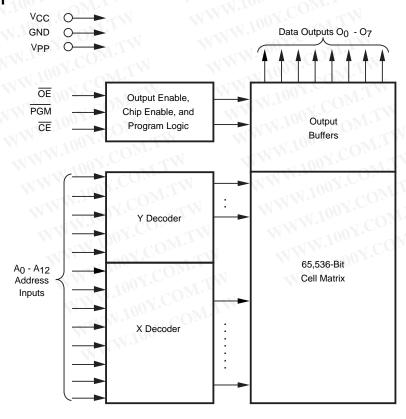
suited for high volume production applications where cost is an important factor and programming only needs to be done once.

This family of EPROMs are fabricated with Fairchild's proprietary, time proven CMOS double-poly silicon gate technology which combines high performance and high density with low power consumption and excellent reliability.

### **Features**

- High performance CMOS
  - -150 ns access time
- JEDEC standard pin configuration
  - —28-pin Plastic DIP package
  - -28-pin CERDIP package
- Drop-in replacement for 27C64 or 2764
- Manufacturers identification code

### **Block Diagram**



DS008634-1

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## VWW.100Y.COM.TW Connection Diagram

WWW.19

WWW

WWW.100Y.CC WWW.100Y.C

Conn	ection	n Diag	gram	W.1	001.	COM	TY	Ń	W	-11				5-83298 com. tw	
	27C512 27512	27C256 27256	27C128 27128	27C32 2732	27C16 2716	Y.CO	NMC	27C64	7	27C16 2716	27C32 2732	27C128 27128	27C256 27256	27C512 27512	
	A <sub>15</sub>	V <sub>PP</sub>	VPP	1	x 10	Vpp□	1	28	□Vcc	M. A.	N.10	Vcc	Vcc	Vcc	
	A <sub>12</sub>	A12	A12	WW	14.	A12□	2	27	□PGM	WW	- 40	PGM	A14	A14	
	A7	A <sub>7</sub>	A <sub>7</sub>	A7	A7	A7 ☐	3	26	□NC	Vcc	Vcc	A13	A13	A13	
	A <sub>6</sub>	A <sub>6</sub>	A <sub>6</sub>	A <sub>6</sub>	A <sub>6</sub>	A6□	4	25	_A8	A8	A8	A8	A8	A8	
	A <sub>5</sub>	A <sub>5</sub>	A <sub>5</sub>	A <sub>5</sub>	A <sub>5</sub>	A5□	5	24	□A9	A9	A9	A9	A9	A9	
	A <sub>4</sub>	A <sub>4</sub>	A <sub>4</sub>	A <sub>4</sub>	A <sub>4</sub>	A4 ☐	6	23	□A11	VPP	A11	A11	A11	A11	κī
	A <sub>3</sub>	A <sub>3</sub>	А3	A3	Аз	A3 🗆	7	22	OE	OE \	OE/V <sub>PP</sub>	OE	ŌĒ	OE/V <sub>PP</sub>	
	A2	A <sub>2</sub>	A <sub>2</sub>	A <sub>2</sub>	A <sub>2</sub>	A2□	8	21	□A10	A10	A10	A10	A10	A10	1
	A <sub>1</sub>	A <sub>1</sub>	A <sub>1</sub>	A <sub>1</sub>	A <sub>1</sub>	A1 □	9	20	CE	CE/PGM	CE	CE	CE/PGM	CE	
	A <sub>0</sub>	A <sub>0</sub>	A <sub>0</sub>	A <sub>0</sub>	A <sub>0</sub>	Ao □	10	19	□07	07	07	07	07	07	1
	00	00	00	00	00	00□	11	18	□06	06	06	06	06	06	
	01	01	01	01	01	01□	12	17	□05	05	05	05	05	05	1.
	02	02	02	02	02	02□	13	16	04	04	04	04	04	04	
	GND	GND	GND	GND	GND	GND□	14	15	□O <sub>3</sub>	03	03	03	03	03	O
	1	7	1		1				_		1				

Note: Socket compatible EPROM pin configurations are shown in the blocks adjacent to the NMC27C64 pins.

### DS008634-2 WWW.100Y.COM.T

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### WWW.100Y.COM.T **Pin Names**

tarries		
	A0-A12	Addresses
	CE	Chip Enable
	ŌĒ	Output Enable
	O <sub>0</sub> -O <sub>7</sub>	Outputs
	PGM	Program
	NC	No Connect
	V <sub>PP</sub>	Programming Voltage
	V <sub>cc</sub>	Power Supply
	GND	Ground
		- W.M.

# Commercial Temperature Range V<sub>CC</sub> = 5V ±10%

Parameter/Order Number	Access Time (ns)
NMC27C64Q, N 150	150
NMC27C64Q, N 200	200

Parameter/Order Number	Access Time (ns
NMC27C64QE, NE200	200

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**Absolute Maximum Ratings** (Note 1)

Temperature Under Bias -55°C to +125°C

Storage Temperature -65°C to +150°C

All Input Voltages except A9

with Respect to Ground (Note 10) +6.5V to -0.6V

All Output Voltages

with Respect to Ground (Note 10)V<sub>CC</sub> +1.0V to GND -0.6V

V<sub>PP</sub> Supply Voltage and A<sub>9</sub> with Respect to Ground

During Programming

+14.0V to -0.6V

V<sub>CC</sub> Supply Voltage with

Respect to Ground +7.0V to -0.6V **Power Dissipation** 1.0W

Lead Temperature

(Soldering, 10 sec.) 300°C

**ESD Rating** 

(Mil Spec 883C, Method 3015.2)

2000V

### **Operating Conditions** (Note 7)

Temperature Range

NMC27C64Q 150, 200 0°C to +70°C

NMC27C64N 150, 200

NMC27C64QE 200 -40°C to +85°C

NMC27C64NE 200

V<sub>CC</sub> Power Supply +5V ±10%

### **READ OPERATION**

### **DC Electrical Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
l <sub>u</sub>	Input Load Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	TV	WW	10	μА	
I <sub>LO</sub>	Output Leakage Current	$V_{OUT} = V_{CC}$ or GND, $\overline{CE} = V_{IH}$		4311	10	μΑ	
I <sub>CC1</sub> (Note 9)	$V_{CC}$ Current (Active) $\overline{CE} = V_{IL}$ , f=5 MHz TTL Inputs Inputs = $V_{IH}$ or $V_{IL}$ , I/O = 0 mA		VIIN	5	20	mA	
I <sub>CC2</sub> (Note 9)	V <sub>CC</sub> Current (Active) CMOS Inputs	$\overline{\text{CE}} = \text{GND}, \text{ f} = 5 \text{ MHz}$ Inputs = $V_{\text{CC}}$ or GND, I/O = 0 mA	OM.TW	3	10	mA	
I <sub>CCSB1</sub>	V <sub>CC</sub> Current (Standby) TTL Inputs	CE = V <sub>IH</sub>	COWIL	0.1	1 WWW.	mA	
I <sub>CCSB2</sub>	V <sub>CC</sub> Current (Standby) CMOS Inputs	CE = V <sub>CC</sub>	I.COM.T	0.5	100	μА	
I <sub>PP</sub>	VPP Load Current	$V_{PP} = V_{CC}$	N.C.	10	μΑ	W.100	
V <sub>IL</sub>	Input Low Voltage	WWW.	-0.1	TW	0.8	V	
V <sub>IH</sub>	Input High Voltage	DM. TANAN.	2.0	WT	V <sub>CC</sub> +1	V	
V <sub>OL1</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1 mA	N.CO	W. TV	0.45	V	
V <sub>OH1</sub>	Output High Voltage	I <sub>OH</sub> = -400 μA	2.4	M	1	V	
V <sub>OL2</sub>	Output Low Voltage	$I_{OL} = 0 \mu A$	N.100	$O_{M,T}$	0.1	V	
V <sub>OH2</sub>	Output High Voltage	I <sub>OH</sub> = 0 μA	V <sub>CC</sub> - 0.1	JOM.	1	V	

### AC Electrical Characteristics

	TVN	in COM.		NMC	27C64		
Symbol	Parameter	Conditions	150		200, E200		Units
		N. TO COM.	Min	Max	Min	Max	1
t <sub>ACC</sub>	Address to Output Delay	CE = OE = V <sub>IL</sub> PGM = V <sub>IH</sub>	W	150		200	ns
t <sub>CE</sub>	CE to Output Delay	$\overline{OE} = V_{IL}, \overline{PGM} = V_{IH}$		150		200	ns
t <sub>OE</sub>	OE to Output Delay	$\overline{CE} = V_{IL}, \overline{PGM} = V_{IH}$		60		60	ns
t <sub>DF</sub>	OE High to Output Float	$\overline{CE} = V_{IL}, \overline{PGM} = V_{IH}$	0	60	0	60	ns
t <sub>CF</sub>	CE High to Output Float	$\overline{OE} = V_{IL}, \overline{PGM} = V_{IH}$	0	60	0	60	ns
t <sub>OH</sub>	Output Hold from Addresses, CE or OE , Whichever Occurred First	CE = OE = V <sub>IL</sub> PGM = V <sub>IH</sub>	0		0		ns

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### Capacitance TA = +25°C, f = 1 MHz (Note 2) NMC27C64Q

Symbol	Parameter	Conditions	Тур	Max	Units
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	6	8	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	<b>4</b> 9	12	pF

### Capacitance TA = +25°C, f = 1 MHz (Note 2) NMC27C64N

Symbol	Parameter	Conditions	Тур	Max	Units	
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	5	10	pF	
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	8	10	pF	

### **AC Test Conditions**

Output Load 1 TTL Gate and  $C_1 = 100 \text{ pF}$  (Note 8)

Input Rise and Fall Times ≤5 ns

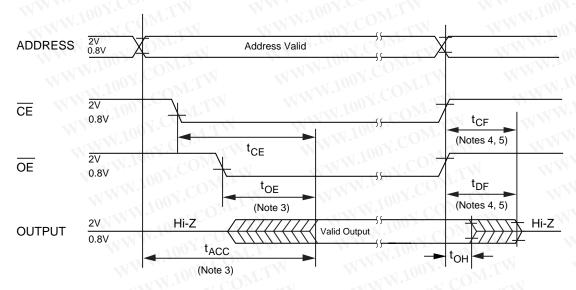
Input Pulse Levels 0.45V to 2.4V

Timing Measurement Reference Level

 Inputs
 0.8V and 2V

 Outputs
 0.8V and 2V

### AC Waveforms (Note 6) (Note 9)



Note 1: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note 2: This parameter is only sampled and is not 100% tested.

Note 3:  $\overline{\text{OE}}$  may be delayed up to  $t_{\text{ACC}}$  -  $t_{\text{OE}}$  after the falling edge of  $\overline{\text{CE}}$  without impacting  $t_{\text{ACC}}$ .

Note 4: The  $t_{DF}$  and  $t_{CF}$  compare level is determined as follows: High to TRI-STATE  $\circledR$ , the measured  $V_{OH1}$  (DC) , 0.10V;

Low to TRI-STATE, the measured  $V_{OL1}$  (DC) + 0.10V. Note 5: TRI-STATE may be attained using  $\overline{OE}$  or  $\overline{CE}$ .

Note 6: The power switching characteristics of EPROMs require careful device decoupling. It is recommended that at least a 0.1 μF ceramic capacitor be used on every device between V<sub>CC</sub> and GND.

Note 7: The outputs must be restricted to  $V_{CC}$  + 1.0V to avoid latch-up and device damage.

Note 8: 1 TTL Gate:  $I_{OL}$  = 1.6 mA,  $I_{OH}$  = -400  $\mu$ A.

C<sub>L</sub>: 100 pF includes fixture capacitance.

Note 9: V<sub>PP</sub> may be connected to V<sub>CC</sub> except during programming.

Note 10: Inputs and outputs can undershoot to -2.0V for 20 ns  ${\rm Max}.$ 

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### WWW.100Y.COM.TW Programming Characteristics (Note 11) (Note 12) (Note 13) (Note 14)

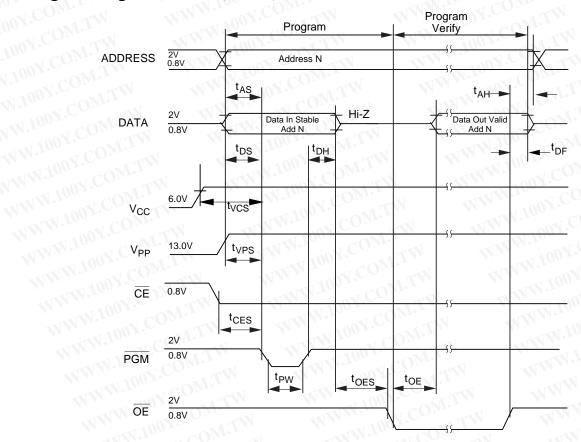
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Symbol	Parameter	Conditions	Min	Тур	Max	Units
t <sub>AS</sub>	Address Setup Time	TW	2	007.0	MIW	μs
t <sub>OES</sub>	OE Setup Time	COMMETAL	2	107.CC	WILL	μs
t <sub>CES</sub>	CE Setup Time	COMP	2	ONY.C	ON	μs
t <sub>DS</sub>	Data Setup Time	CONT	2		COMP	μs
t <sub>VPS</sub>	V <sub>PP</sub> Setup Time	COM	2	1100	COMP.	μs
t <sub>vcs</sub>	V <sub>CC</sub> Setup Time	W. Th	2	IN 100 3	COM	μs
t <sub>AH</sub>	Address Hold Time	OOY. COM.TW	0	W.100	MOD.	μs
t <sub>DH</sub>	Data Hold Time	1001.COLUTY	2	10	OY.C	μs
t <sub>DF</sub>	Output Enable to Output Float Delay	CE = V <sub>IL</sub>	0	WW.	130	ns
t <sub>PW</sub>	Program Pulse Width	W.1007.	0.45	0.5	0.55	ms
t <sub>OE</sub>	Data Valid from OE	CE = V <sub>IL</sub>	11/1	N. V.	150	ns
I <sub>PP</sub>	V <sub>PP</sub> Supply Current During Programming Pulse	$\frac{\overline{CE} = V_{IL}}{\overline{PGM} = V_{IL}}$	TIN	MAN	30	mA
I <sub>cc</sub>	V <sub>CC</sub> Supply Current	WW.100 1 CO	N. I		10	mA
T <sub>A</sub>	Temperature Ambient	M. 1007.	20	25	30	°C
V <sub>CC</sub>	Power Supply Voltage	MM 1 100 X 10	5.75	6.0	6.25	V
V <sub>PP</sub>	Programming Supply Voltage	MAN 100 X.C	12.2	13.0	13.3	V
t <sub>FR</sub>	Input Rise, Fall Time	MMM. 100X.	5		MM	ns
V <sub>IL</sub>	Input Low Voltage	MMMino	CONT	0.0	0.45	V.
V <sub>IH</sub>	Input High Voltage	WW.100	2.4	4.0	WWW	V
t <sub>IN</sub>	Input Timing Reference Voltage	W 100	0.8	1.5	2.0	V
t <sub>OUT</sub>	Output Timing Reference Voltage	71 10	0.8	1.5	2.0	V

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### **Programming Waveforms** (Note 13)

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Note 11: Fairchild's standard product warranty applies to devices programmed to specifications described herein.

Note 12:  $V_{CC}$  must be applied simultaneously or before  $V_{PP}$  and removed simultaneously or after  $V_{PP}$ . The EPROM must not be inserted into or removed from a board with voltage applied to  $V_{PP}$  or  $V_{CC}$ .

Note 13: The maximum absolute allowable voltage which may be applied to the V<sub>PP</sub> pin during programming is 14V. Care must be taken when switching the V<sub>PP</sub> supply to prevent any overshoot from exceeding this 14V maximum specification. At least a 0.1 μF capacitor is required across V<sub>PP</sub>, V<sub>CC</sub> to GND to suppress spurious voltage transients which may damage the device.

Note 14: Programming and program verify are tested with the interactive Program Algorithm, at typical power supply voltages and timings.

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### Functional Description DEVICE OPERATION

The six modes of operation of the NMC27C64 are listed in Table 1. It should be noted that all inputs for the six modes are at TTL levels. The power supplies required are  $V_{\rm CC}$  and  $V_{\rm PP}$ . The  $V_{\rm PP}$  power supply must be at 12.75V during the three programming modes, and must be at 5V in the other three modes. The  $V_{\rm CC}$  power supply must be at 6V during the three programming modes, and at 5V in the other three modes.

### **Read Mode**

The NMC27C64 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable  $(\overline{CE})$  is the power control and should be used for device selection. Output Enable  $(\overline{OE})$  is the output control and should be used to gate data to the output pins, independent of device selection. The programming pin  $(\overline{PGM})$  should be at  $V_{IH}$  except during programming. Assuming that addresses are stable, address access time  $(t_{ACC})$  is equal to the delay from  $\overline{CE}$  to output  $(t_{CE})$ . Data is available at the outputs  $t_{OE}$  after the falling edge of OE , assuming that  $\overline{CE}$  has been low and addresses have been stable for at least  $t_{ACC}-t_{OF}$ .

The sense amps are clocked for fast access time.  $V_{CC}$  should therefore be maintained at operating voltage during read and verify. If  $V_{CC}$  temporarily drops below the spec. voltage (but not to ground) an address transition must be performed after the drop to insure proper output data.

### **Standby Mode**

The NMC27C64 has a standby mode which reduces the active power dissipation by 99%, from 55 mW to 0.55 mW. The NMC27C64 is placed in the standby mode by applying a CMOS high signal to the  $\overline{\text{CE}}$  input. When in standby mode, the outputs are in a high impedance state, independent of the  $\overline{\text{OE}}$  input.

#### **Output OR-Tying**

Because NMC27C64s are usually used in larger memory arrays, Fairchild has provided a 2-line control function that accommodates this use of multiple memory connections. The 2-line control function allows for:

- 1. the lowest possible memory power dissipation, and
- complete assurance that output bus contention will not occur.

To most efficiently use these two control lines, it is recomended that  $\overline{CE}$  (pin 20) be decoded and used as the primary device selecting function, while  $\overline{OE}$  (pin 22) be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low power standby modes and that the output pins are active only when data is desired from a particular memory device.

### **Programming**

CAUTION: Exceeding 14V on pin 1 ( $V_{PP}$ ) will damage the NMC27C64.

Initially, all bits of the NMC27C64 are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be presented in the data word. A "0" cannot be changed to a "1" once the bit has been programmed.

The NMC27C64 is in the programming mode when the V<sub>PP</sub> power supply is at 12.75V and  $\overline{OE}$  is at V<sub>IH</sub>. It is required that at least a 0.1 µF capacitor be placed across V<sub>PP</sub>, V<sub>CC</sub> to ground to suppress spurious voltage transients which may damage the device. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

For programming,  $\overline{\text{CE}}$  should be kept TTL low at all times while  $V_{\text{PP}}$  is kept at 12.75V.

When the address and data are stable, an active low, TTL program pulse is applied to the  $\overline{PGM}$  input. A program pulse must be applied at each address location to be programmed. The NMC27C64 is programmed with the Fast Programming Algorithm shown in Figure 1. Each address is programmed with a series of 100  $\mu s$  pulses until it verfies good, up to a maximum of 25 pulses. Most memory cells will program with a single 100  $\mu s$  pulse. The NMC27C64 must not be programmed with a DC signal applied to the PGM input.

Programming multiple NMC27C64s in parallel with the same data can be easily accomplished due to the simplicity of the programming requirements. Like inputs of the paralleled NMC27C64s may be connected together when they are programmed with the same data. A low level TTL pulse applied to the  $\overline{PGM}$  input programs the paralleled NMC27C64s. If an application requires erasing and reprogramming, the NMC27C64Q UV erasable PROM in a windowed package should be used.

**TABLE 1. Mode Selection** 

Pins Mode	CE (20)	OE (22)	PGM (27)	V <sub>PP</sub> (1)	V <sub>CC</sub> (28)	Outputs (11–13, 15–19)
Read	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	5V	5V	D <sub>OUT</sub>
Standby	V <sub>IH</sub>	Don't Care	Don't Care	5V	5V	Hi-Z
Output Disable	Don't Care	V <sub>IH</sub>	V <sub>IH</sub>	5V	5V	Hi-Z
Program	V <sub>IL</sub>	V <sub>IH</sub>		13V	6V	D <sub>IN</sub>
Program Verify	V <sub>IL</sub>	$V_{IL}$	V <sub>IH</sub>	13V	6V	D <sub>OUT</sub>
Program Inhibit	V <sub>IH</sub>	Don't Care	Don't Care	13V	6V	Hi-Z

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### Functional Description (Continued)

### **Program Inhibit**

Programming multiple NMC27C64s in parallel with different data is also easily accomplished. Except for CE all like inputs (including OE and PGM) of the parallel NMC27C64 may be common. A TTL low level program pulse applied to an NMC27C64's PGM input with CE at  $\rm V_{IL}$  and  $\rm V_{PP}$  at 13.0V will program that NMC27C64. A TTL high level CE input inhibits the other NMC27C64s from being programmed.

#### **Program Verify**

A verify should be performed on the programmed bits to determine whether they were correctly programmed. The verify may be performed with  $V_{PP}$  at 13.0V.  $V_{PP}$  must be at  $V_{CC}$ , except during programming and program verify.

#### MANUFACTURER'S IDENTIFICATION CODE

The NMC27C64 has a manufacturer's identification code to aid in programming. The code, shown in Table 2, is two bytes wide and is stored in a ROM configuration on the chip. It identifies the manufacturer and the device type. The code for the NMC27C64 is "8FC2", where "8F" designates that it is made by Fairchild Semiconductor, and "C2" designates a 64k part.

The code is accessed by applying 12V  $\pm$  0.5V to address pin A9. Addresses A1–A8, A10–A12, CE, and OE are held at V $_{IL}$ . Address A0 is held at V $_{IL}$  for the manufacturer's code, and at V $_{IH}$  for the device code. The code is read out on the 8 data pins. Proper code access is only guaranteed at 25°C  $\pm$ 5°C.

The primary purpose of the manufacturer's identification code is automatic programming control. When the device is inserted in a EPROM programmer socket, the programmer reads the code and then automatically calls up the specific programming algorithm for the part. This automatic programming control is only possible with programmers which have the capability of reading the code.

#### **ERASURE CHARACTERISTICS**

The erasure characteristics of the NMC27C64 are such that erasure begins to occur when exposed to light with wavelengths shorter than approximately 4000 Angstroms (Å). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000Å – 4000Å range.

After programming, opaque labels should be placed over the NMC27C64's window to prevent unintentional erasure. Covering the window will also prevent temporary functional failure due to the generation of photo currents.

The recommended erasure procedure for the NMC27C64 is exposure to short wave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity x exposure time) for erasure should be a minimum of 15W-sec/cm<sup>2</sup>.

The NMC27C64 should be placed within 1 inch of the lamp tubes during erasure. Some lamps have a filter on their tubes which should be removed before erasure.

An erasure system should be calibrated periodically. The distance from lamp to unit should be maintained at one inch. The erasure time increases as the square of the distance. (If distance is doubled the erasure time increases by a factor of 4.) Lamps lose intensity as they age. When a lamp is changed, the distance has changed or the lamp has aged, the system should be checked to make certain full erasure is occurring. Incomplete erasure will cause symptoms that can be misleading. Programmers, components, and even system designs have been erroneously suspected when incomplete erasure was the problem.

#### SYSTEM CONSIDERATION

The power switching characteristics of EPROMs require careful decoupling of the devices. The supply current,  $I_{CC}$ , has three segments that are of interest to the system designer—the standby current level, the active current level, and the transient current peaks that are produced by voltage transitions on input pins. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. The associated  $\rm V_{\rm CC}$ transient voltage peaks can be suppressed by properly selected decoupling capacitors. It is recommended that at least a 0.1 µF ceramic capacitor be used on every device between V<sub>CC</sub> and GND. This should be a high frequency capacitor of low inherent inductance. In addition, at least a 4.7 µF bulk electrolytic capacitor should be used between  $V_{CC}$  and GND for each eight devices. The bulk capacitor should be located near where the power supply is connected to the array. The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of the PC board traces.

**TABLE 2. Manufacturer's Identification Code** 

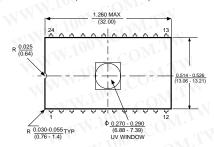
Pins	A0 (10)	O7 (19)	O6 (18)	O5 (17)	O4 (16)	O3 (15)	O2 (13)	O1 (12)	O0 (11)	Hex Data
Manufacturer Code	V <sub>IL</sub>	11	000	0	0	1	1,00	V.GO.	11	8F
Device Code	V <sub>IH</sub>	1	1 (	0	0	0	0	100	0	C2

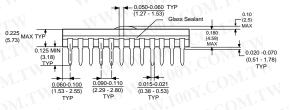
9

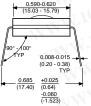
**EPRON** 

特力材料886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www. 100y. com. tw

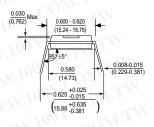
### Physical Dimensions inches (millimeters) unless otherwise noted

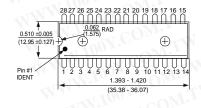


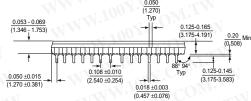




Dual-In-Line Package (Q) Order Number NMC27C64Q Package Number J28AQ







**Dual-In-Line Package (N)** Order Number NMC27C64N Package Number N28B

### **Life Support Policy**

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Fairchild Semiconductor Tel. 1-888-522-5372

Fairchild Semiconductor Deutsch +49 (0) 8141-6102-0 English Français Italiano +44 (0) 1793-856856 +33 (0) 1-6930-3696 +39 (0) 2-249111-1 Fairchild Semiconductor Hong Kong 8/F, Room 808, Empire Centre

68 Mody Road, T simshatsui East Kowloon. Hong Kong Tel; +852-2722-8388 Fax: +852-2722-8383

Fairchild Semiconductor Japan Ltd. 4F, Natsume Bldg.

Z-18-6, Yushima, Bunkyo-ku Tokyo, 113-0034 Japan Tel: 81-3-3818-8840 Fax: 81-3-3818-8841

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